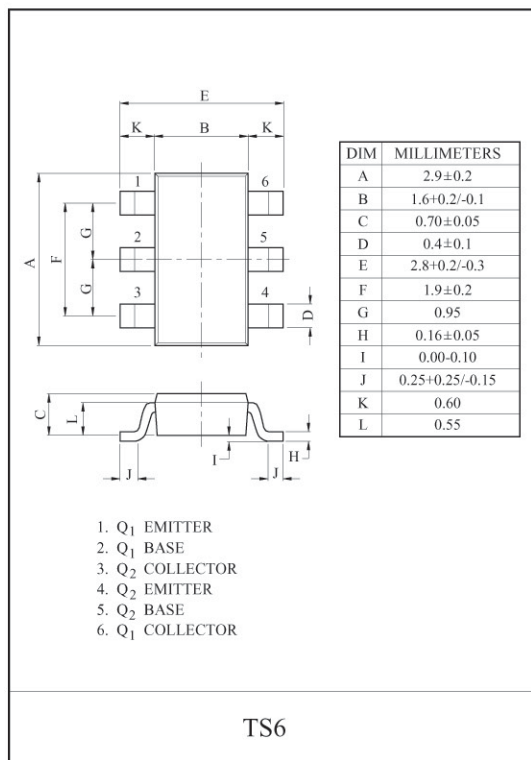
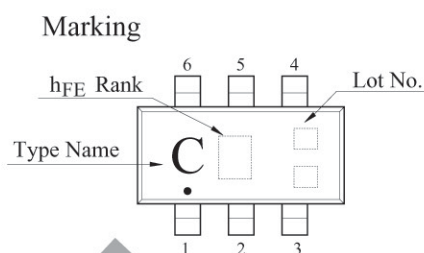
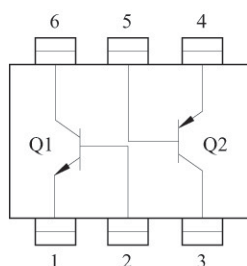


GENERAL PURPOSE APPLICATION.

FEATURES

- Including two devices in TS6.
(Thin Super Mini type with 6 pin)
- Simplify circuit design.
- Reduce a quantity of parts and manufacturing process.

EQUIVALENT CIRCUIT (TOP VIEW)



Q1 MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	35	V
Collector-Emitter Voltage	V _{CE0}	30	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	800	mA
Emitter Current	I _E	-800	mA

Q2 MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-35	V
Collector-Emitter Voltage	V _{CE0}	-30	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-800	mA
Emitter Current	I _E	800	mA

Q1, Q2 MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P _C *	0.9	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C

* Package mounted on a ceramic board (600mm² × 0.8mm)

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Q₁ ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	I_{CBO}	$V_{CB}=35V, I_E=0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	0.1	μA
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE}=1V, I_C=100mA$	100	-	320	
	$h_{FE}(2)$	$V_{CE}=1V, I_C=700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=500mA, I_B=20mA$	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=1V, I_C=10mA$	0.5	-	0.8	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	19	-	pF

Note) $h_{FE}(1)$ Classification O:100~200, Y:160~320.

Q₂ ELECTRICAL CHARACTERISTICS (Ta=25°C)

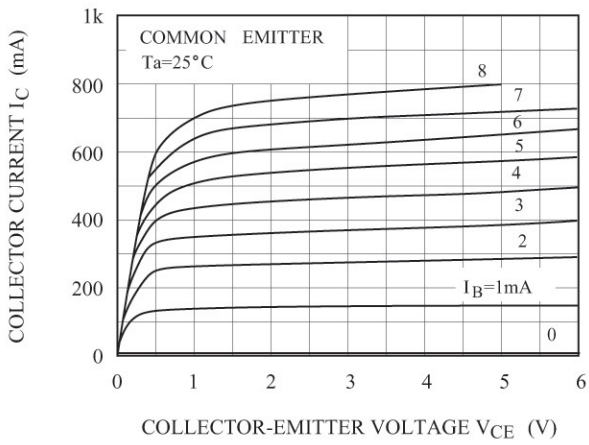
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT.
Collector Cut-off Current	I_{CBO}	$V_{CB}=-35V, I_E=0$	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-0.1	μA
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE}=-1V, I_C=-100mA$	100	-	320	
	$h_{FE}(2)$	$V_{CE}=-1V, I_C=-700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=-500mA, I_B=-20mA$	-	-	-0.7	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$	-0.5	-	-0.8	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	19	-	pF

Note) $h_{FE}(1)$ Classification O:100~200, Y:160~320.

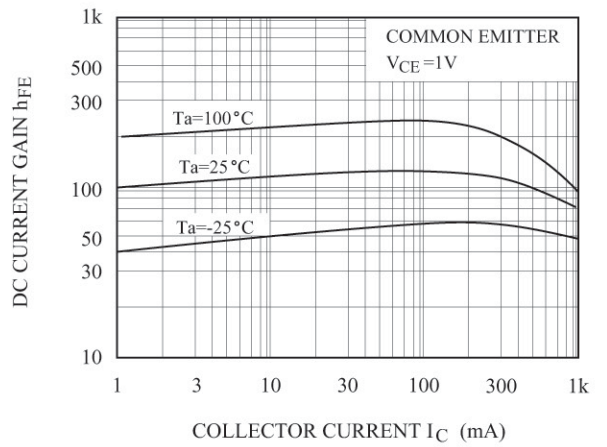
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Q₁ (NPN TRANSISOR)

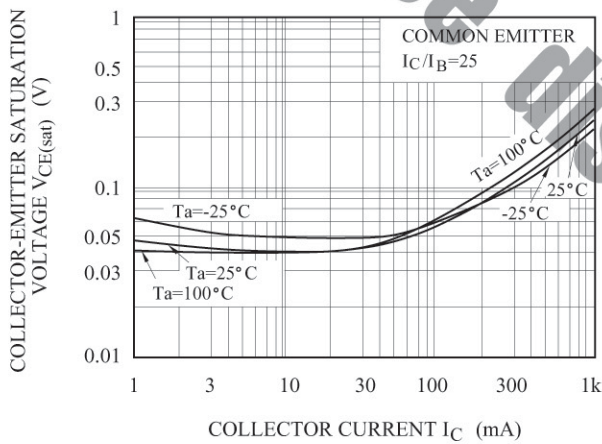
$I_C - V_{CE}$



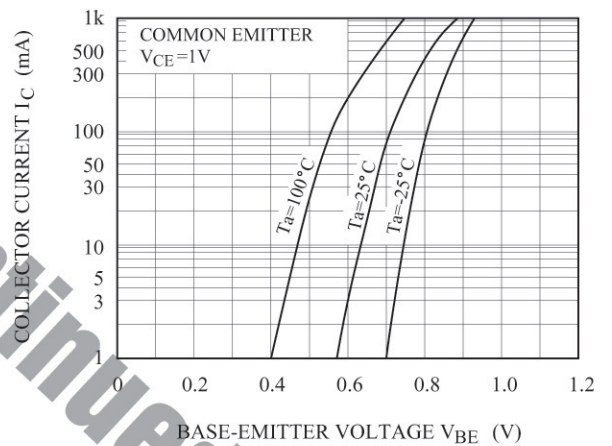
$h_{FE} - I_C$



$V_{CE(sat)} - I_C$

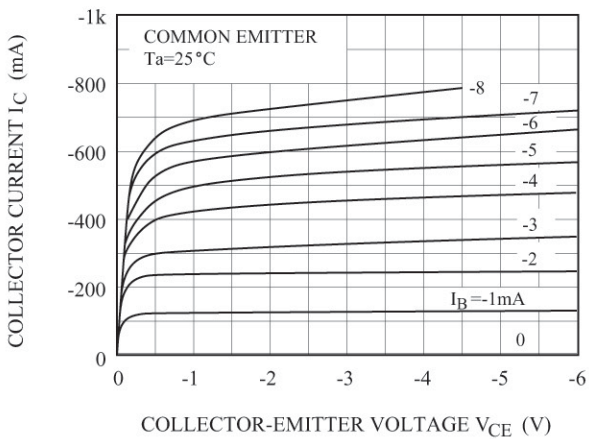


$I_C - V_{BE}$

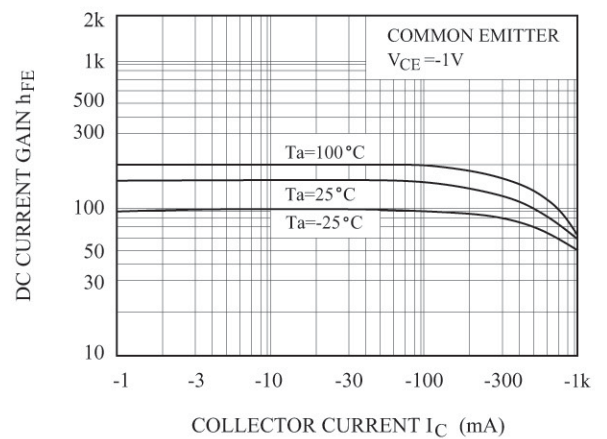


Q₂ (PNP TRANSISOR)

$I_C - V_{CE}$

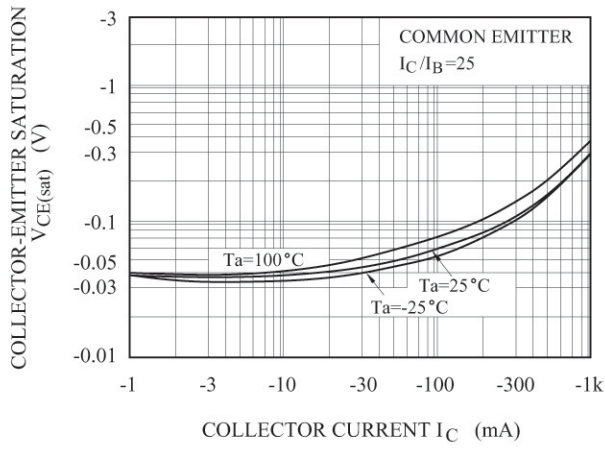


$h_{FE} - I_C$

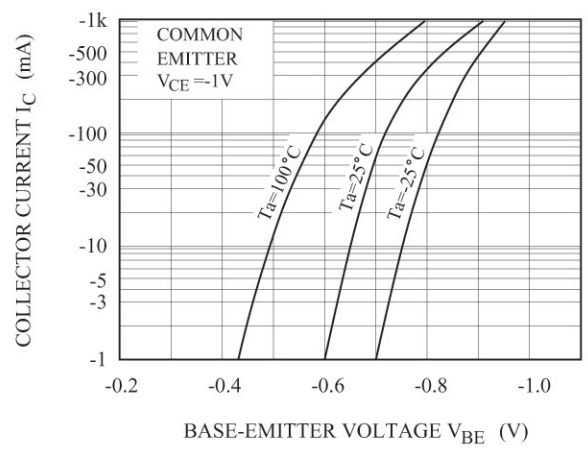


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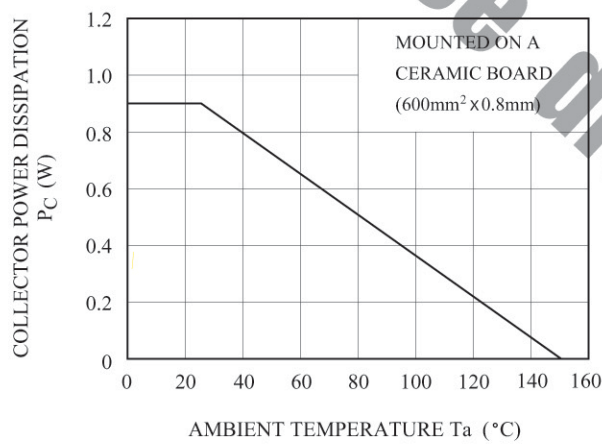
$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



$P_C - T_a$



BEP discontinued